



12/23/96

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 1-1571
PATENT

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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of )  
 Ritu Shrivastava, et al. )  
 Serial No.: 08/456,080 )  
 Filed: May 29, 1996 )  
 For: DRAM CELL WITH SELF- )  
 ALIGNED CONTACT AND )  
 METHOD OF )  
 FABRICATING SAME )

Group Art Unit: 1107

Examiner: H. Tsai

RECEIVED

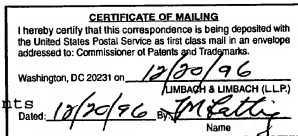
JAN 10 1997

GROUP 1100

RESPONSE TO OFFICE ACTION

MAILED SEPTEMBER 20, 1996

Honorable Commissioner of Patents  
 and Trademarks  
 Washington, D.C. 20231



Sir:

Please amend the above-identified application as follows:

IN THE TITLE:

Please delete the title in its entirety and substitute the following new title:

-- METHOD OF FABRICATING DRAM CELL WITH  
 SELF-ALIGNED CONTACT --

IN THE CLAIMS:

Please amend Claim 6 to read as follows:

1. [Amended] A method of fabricating a dynamic random access memory (DRAM) structure [(100)] in a semiconductor substrate having a first conductivity type, the DRAM structure [(100)] including source [(120)] and drain regions of a second conductivity type that is opposite to the first conductivity type formed in the semiconductor substrate in spaced-apart relationship to define a

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